**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Extended temperature range T<sub>i</sub> = 175 °C
- · Side wettable flanks for optical solder inspection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Trench MOSFET technology
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- · High-speed line driver
- Low-side load switch
- · Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C	-	-	40	V
$V_{GS}$	gate-source voltage		-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C	-	-	19	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C	-	-	15	W
Static characte	eristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 8 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	17	23	mΩ



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	157	D
2	D	drain	7 7	
3	G	gate	2 5	G (F)
4	S	source	3 8 4	mbb076 S
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BUK6D23-40E	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220		

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
BUK6D23-40E	4R

40 V, N-channel Trench MOSFET

# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	40	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
$I_D$	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	19	Α
		V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 100 °C		-	12	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	8	Α
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	76	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C		-	15	W
		T <sub>amb</sub> = 25 °C	[1]	-	2.3	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drai	in diode					,
Is	source current	T <sub>sp</sub> = 25 °C		-	15	Α
		T <sub>amb</sub> = 25 °C	[1]	-	2.3	Α
I <sub>SM</sub>	peak source current	single pulse; $t_p \le 10 \mu s$ ; $T_{sp} = 25 ^{\circ}C$		-	61	Α
ESD maxim	um rating					,
$V_{ESD}$	electrostatic discharge voltage	НВМ	[2]	-	500	V
Avalanche ı	ruggedness			'		
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = 1.35 A; DUT in avalanche (unclamped)		-	28.4	mJ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>2]</sup> Measured between all pins.

#### 40 V, N-channel Trench MOSFET

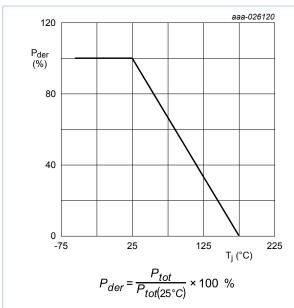


Fig. 1. Normalized total power dissipation as a function of junction temperature

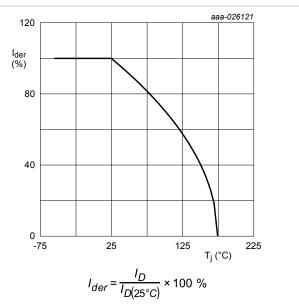


Fig. 2. Normalized continuous drain current as a function of junction temperature

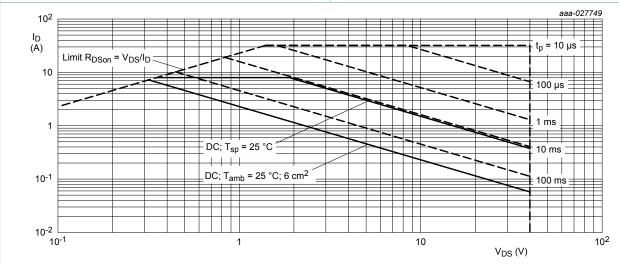


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

40 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	57	66	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	6	10	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

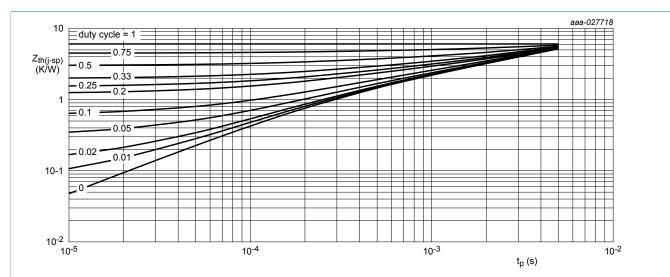


Fig. 4. Transient thermal impedance from junction to solder point as a function of pulse duration; typical values

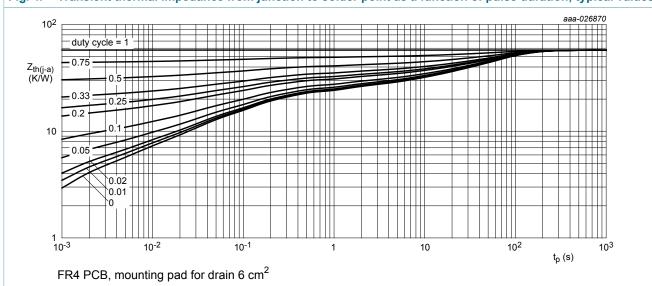


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

40 V, N-channel Trench MOSFET

### 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					,
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	1.3	1.7	2.7	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C	-	17	23	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 175 °C	-	32	43	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 6.3 A; $T_j$ = 25 °C	-	22	30	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7 \text{ A}; T_j = 25 \text{ °C}$	-	33	-	S
$R_G$	gate resistance	f = 1 MHz	-	1.8	-	Ω
Dynamic c	haracteristics					,
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 7 A; V <sub>GS</sub> = 10 V;	-	11	19	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	2	-	nC
$Q_{GD}$	gate-drain charge		-	2.4	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	582	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	101	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	58	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 7 A; V <sub>GS</sub> = 10 V;	-	2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time	_	-	12	-	ns
t <sub>f</sub>	fall time	_	-	5	-	ns
Source-dra	in diode			'	,	
$V_{SD}$	source-drain voltage	$I_S = 2.3 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.8	1.2	V
		1 - 2 2 A d /dt - 400 A /		12.0	_	no
t <sub>rr</sub>	reverse recovery time	$I_S = 2.3 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	12.8	-	ns

#### 40 V, N-channel Trench MOSFET

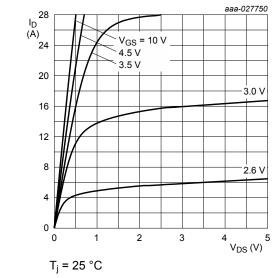


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

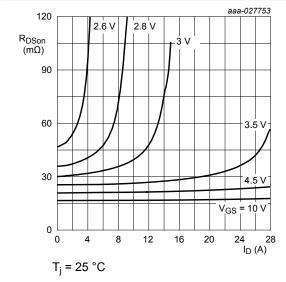


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

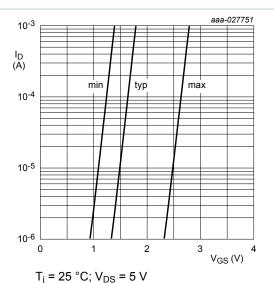


Fig. 7. Sub-threshold drain current as a function of

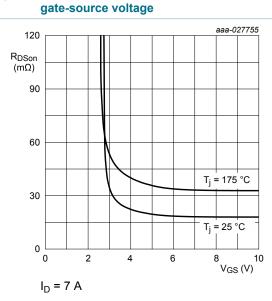


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 40 V, N-channel Trench MOSFET

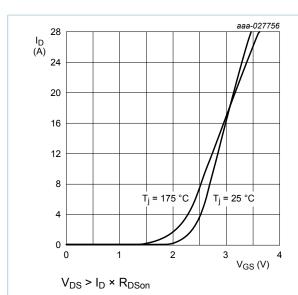


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

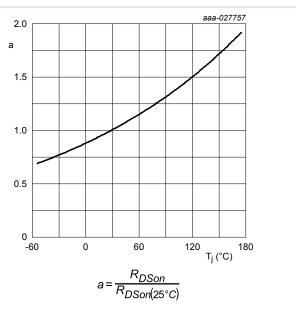


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

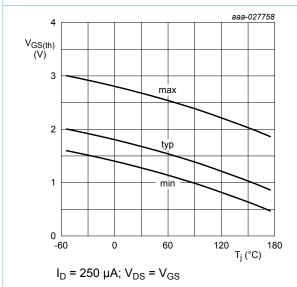


Fig. 12. Gate-source threshold voltage as a function of junction temperature

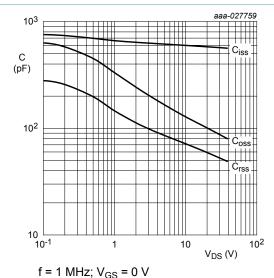


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 40 V, N-channel Trench MOSFET

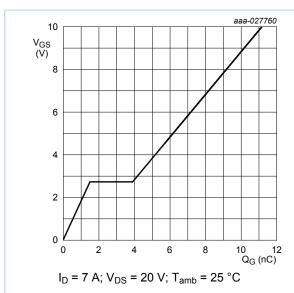


Fig. 14. Gate-source voltage as a function of gate charge; typical values

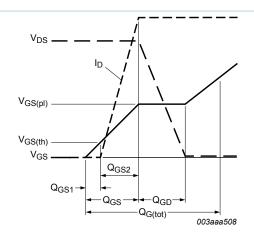


Fig. 15. Gate charge waveform definitions

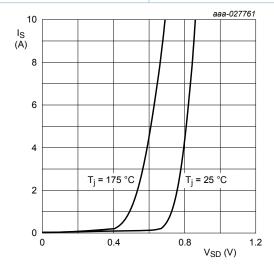
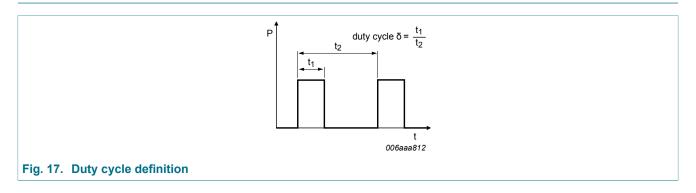


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

40 V, N-channel Trench MOSFET

## 11. Test information

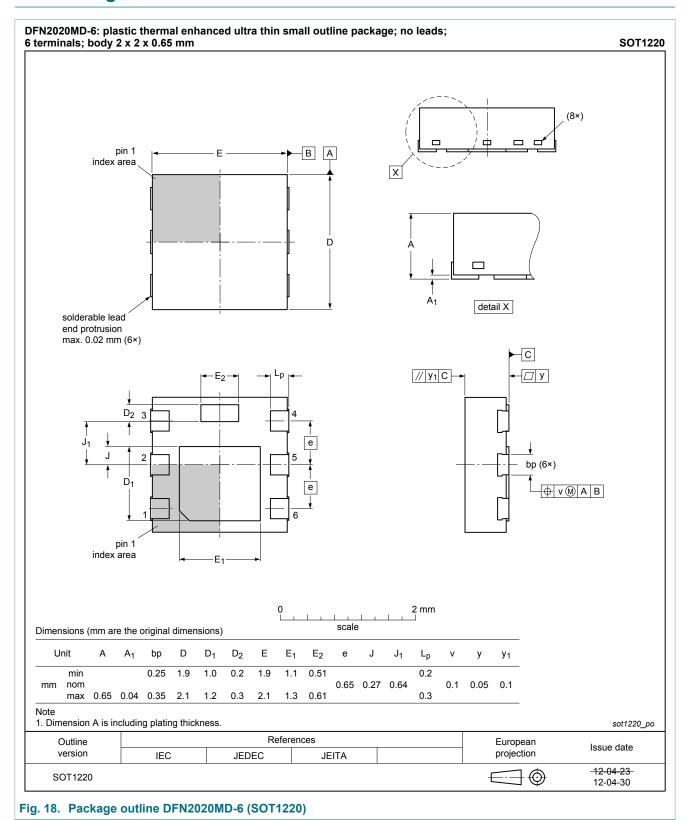


## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

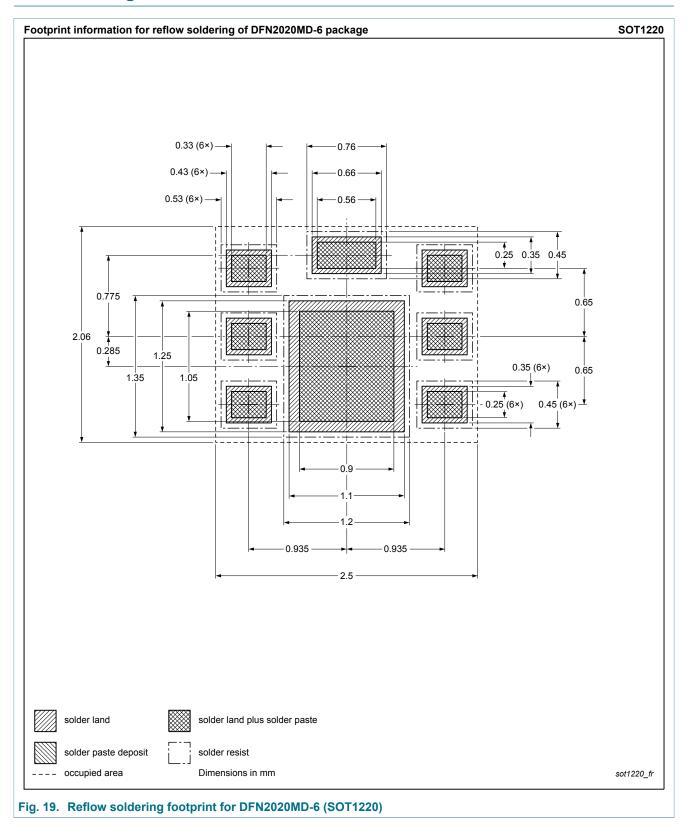
40 V, N-channel Trench MOSFET

## 12. Package outline



40 V, N-channel Trench MOSFET

## 13. Soldering



40 V, N-channel Trench MOSFET

# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BUK6D23-40E v.1	20171213	Product data sheet	-	-

#### 40 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 40 V, N-channel Trench MOSFET

### 16. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10.	Characteristics	б
11.	Test information	. 10
12.	Package outline	11
13.	Soldering	12
14.	Revision history	13
15.	Legal information	. 14

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15 / 15

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